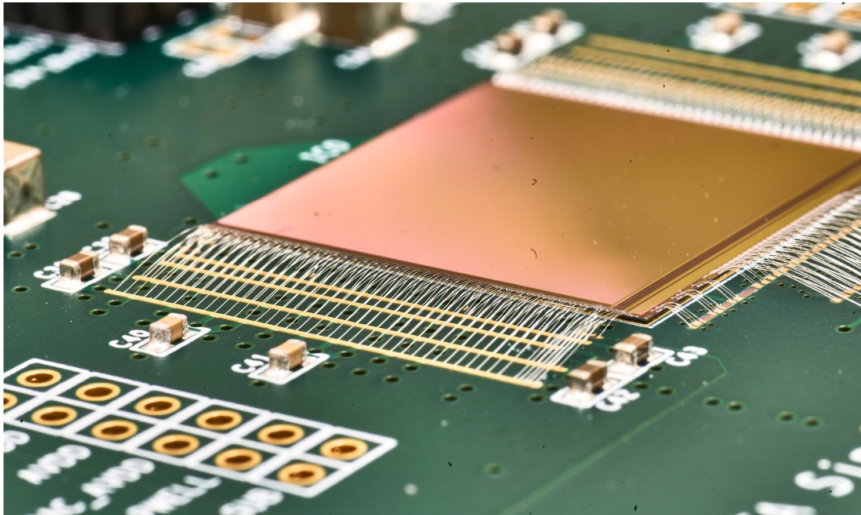


# Radiation hardness and timing performance of MALTA monolithic Pixel sensors in Tower 180 nm

1st DRD3 week on Solid State Detectors R&D WG/WP1

Lucian Fasselt

17 June 2024



## Content

- MALTA beam telescope @ CERN SPS
- Radiation hardness at  $3 \times 10^{15} n_{eq}/cm^2$
- Timing resolution  $\sim 2$  ns
- Depletion depth studies
- MALTA3

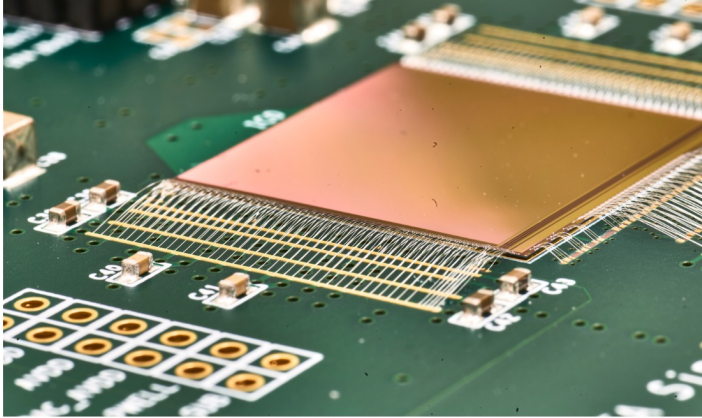
P. Allport (Birmingham), I. Asensi Tortajada (CERN), P. Behera (IITM), D.V. Berlea (DESY), D. Bortoletto (Oxford), C. Buttar (Glasgow), F. Dachs (CERN), V. Dao (CERN), G. Dash (IITM), D. Dobrijevic (Zagreb, CERN), [L. Fasselt \(DESY\)](#), L. Flores Sanz de Acedo (CERN), M. Gazi (Oxford), L. Gonella (Birmingham), V. Gonzalez (Valencia), G. Gustavino (CERN), S. Haberl (CERN, Innsbruck), T. Inada (CERN), P. Jana (IITM), K. Kotsokechagia (CERN), L. Li (Birmingham), H. Pernegger (CERN), P. Riedler (CERN), W. Snoeys (CERN), C.A Solans Sanchez (CERN), T. Suligoj (Zagreb), M. van Rijnbach (CERN), M. Vazquez Nunez (CERN, Valencia), A. Vijay (IITM), J. Weick (CERN), S. Worm (DESY)



UNIVERSITY OF BIRMINGHAM

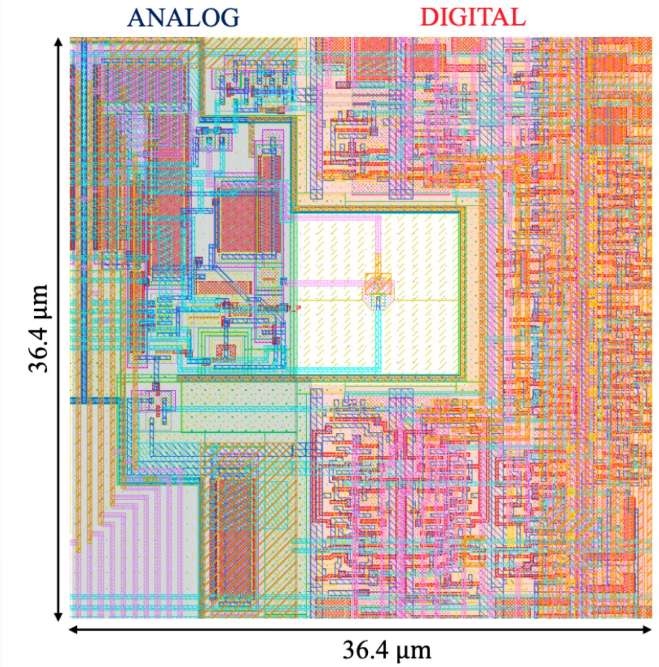
# Origin of MALTA

## Based on R&D for ALPIDE



### MALTA Chip

- 180 nm Tower CMOS imaging process
- $512 \times 512$  pixels
- Originally conceived for ATLAS pixel detector upgrade for HL-LHC
- Timing response **within 25 ns**
- Radiation hard up to  $3 \times 10^{15} n_{eq}/cm^2$   
(ALPIDE  $< 10^{14} n_{eq}/cm^2$ )
- Asynchronous readout of binary hit info  
(see talk tomorrow 9 am by C. Solans)
- No TOT, only binary hit info
- High data rate  **$>100 \text{ MHz}/cm^2$**

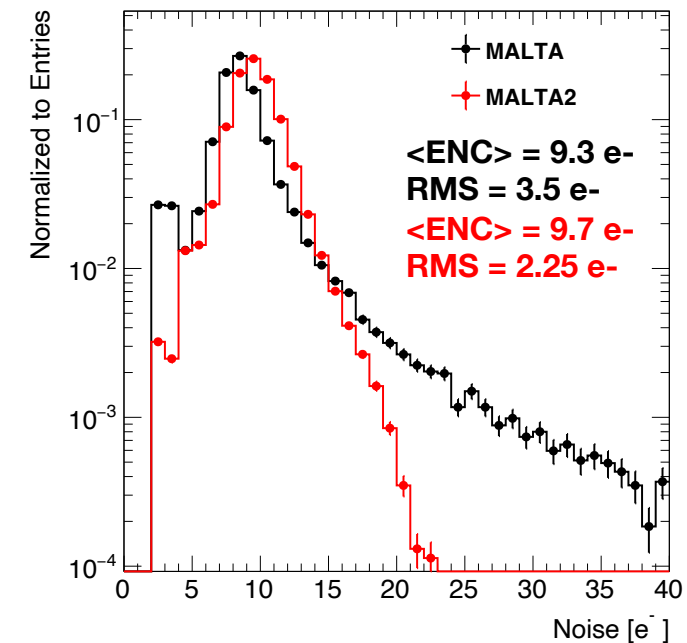
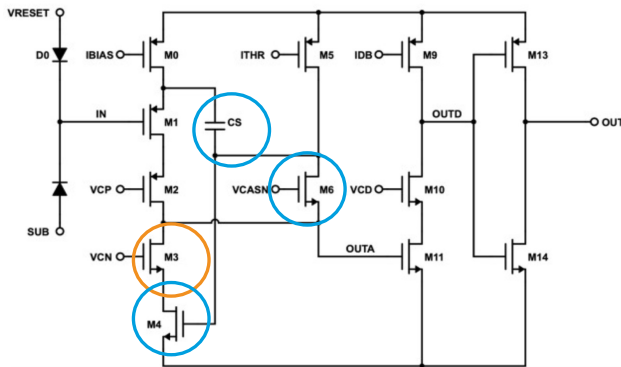


### MALTA Pixel

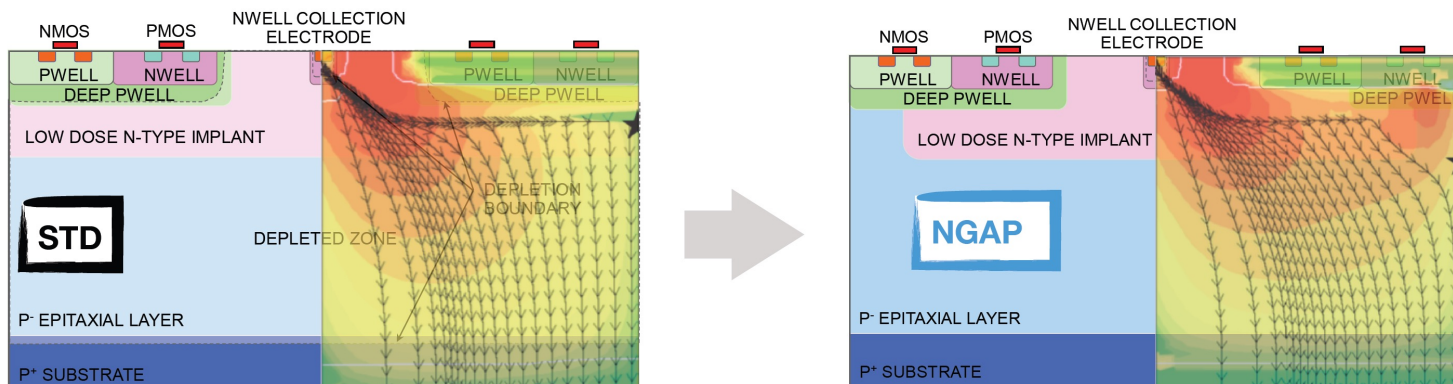
- $36.4 \times 36.4 \mu m^2$  pixel size
- Thickness down to  $50 \mu m$  (up to  $300 \mu m$ )
- $3 \times 3 \mu m^2$  small collection electrode  
→ Small capacitance ( $< 5 \text{ fF}$ )  
→ ENC  $< 15 e^-$
- Low voltage (6 - 30 V)
- **Low power** ( $1 \mu W/\text{pixel}$ )

# MALTA2 modifications

- Improved Front-end
  - Enlarged transistors
  - Cascode stage
    - Lower noise
    - Higher gain
- Pixel variants: Gap in n-layer (NGAP) or extra deep p-well (XDPW)
  - Improved E-field and charge collection in pixel corners
- Epitaxial silicon (30 μm active) in 50 μm thick sensor for minimal material
- Czochralski substrate** (100 to 300 μm)
  - Larger cluster size
  - Larger substrate voltage applicable
  - Improved radiation hardness

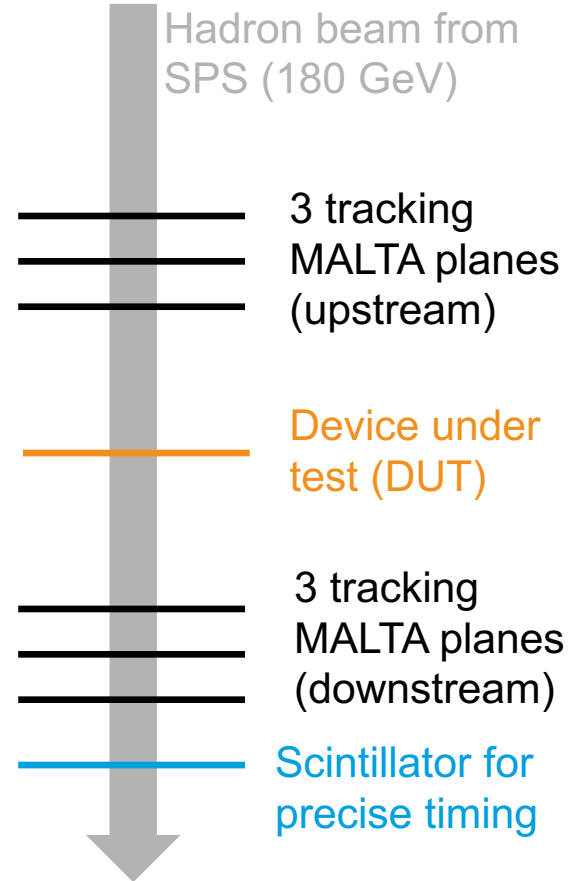
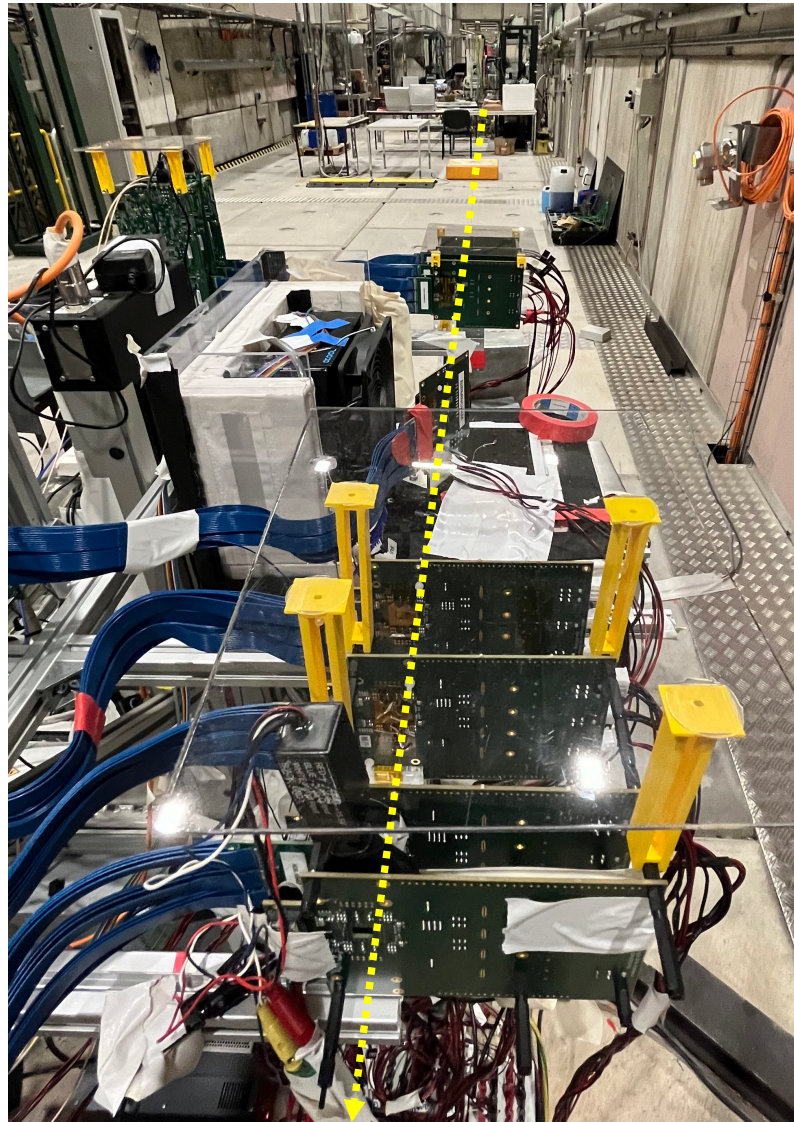


M. Munker et al.,  
JINST C05013

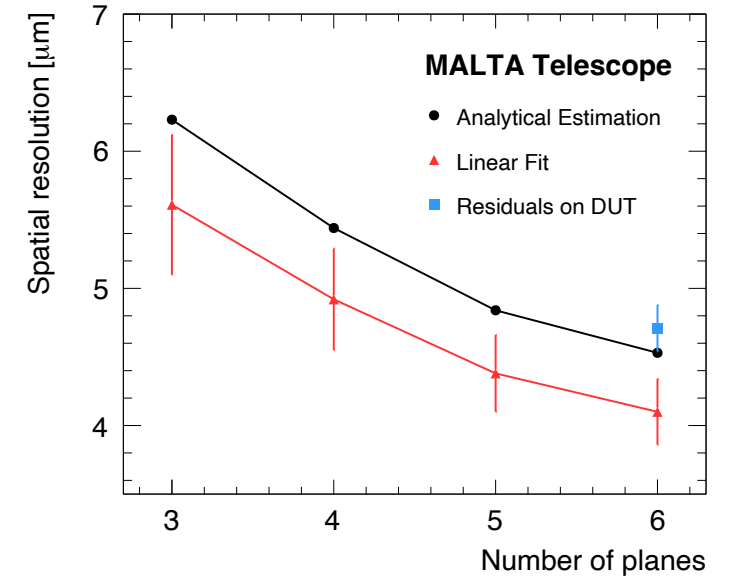


Gap in the low dose N-type implant

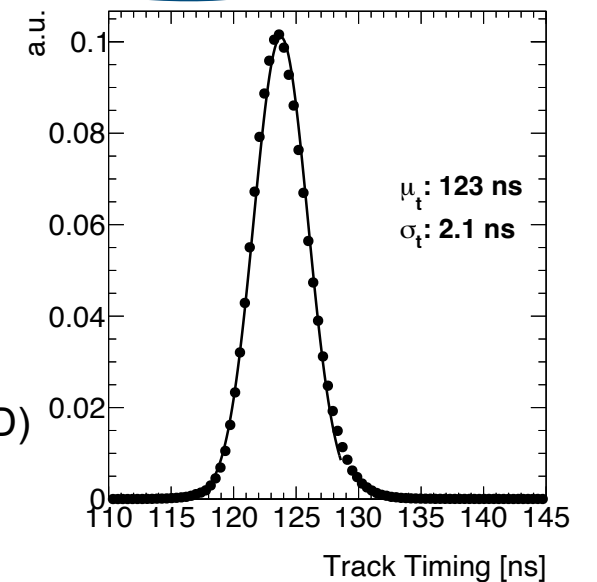
## MALTA telescope @ SPS



- permanently installed at SPS
- Up to 2 DUTs (in coldbox)
- used by other groups for their sensor characterization (e.g. BCM', ATLAS ITk pixel, HGTD)
- low  $X_0$  telescope for material measurement via multiple scattering with PS T9 e- beam

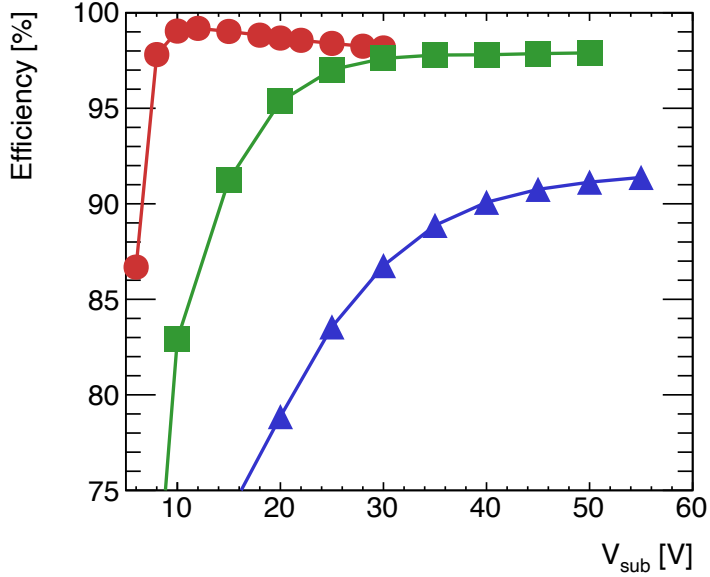


spatial resolution:  $\sigma_s = 4.5 \mu\text{m}$   
 time resolution:  $\sigma_t = 2.1 \text{ ns}$   
 → Reference for DUT



# MALTA2 irradiation study up to $3 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$

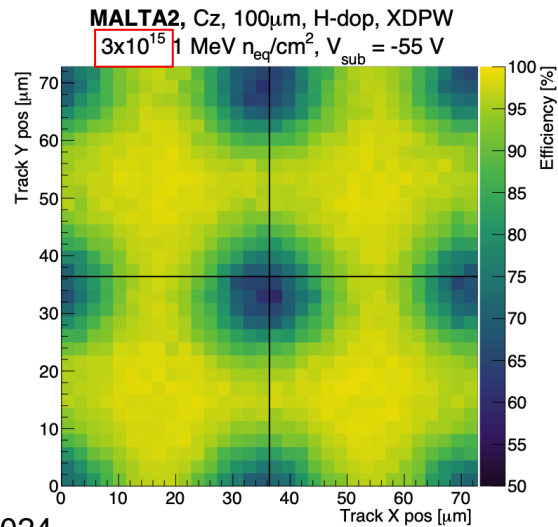
Efficiency > 90 % recovered by substrate voltage increase



**MALTA2**  
Cz, 100 μm, H-dop  
back-metal, XDPW

- $1 \times 10^{15} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$
- $2 \times 10^{15} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$
- ▲  $3 \times 10^{15} \text{ 1 MeV } n_{\text{eq}}/\text{cm}^2$

- Backside metallisation  
→ good voltage propagation to substrate across chip
- Efficiency loss at pixel corners

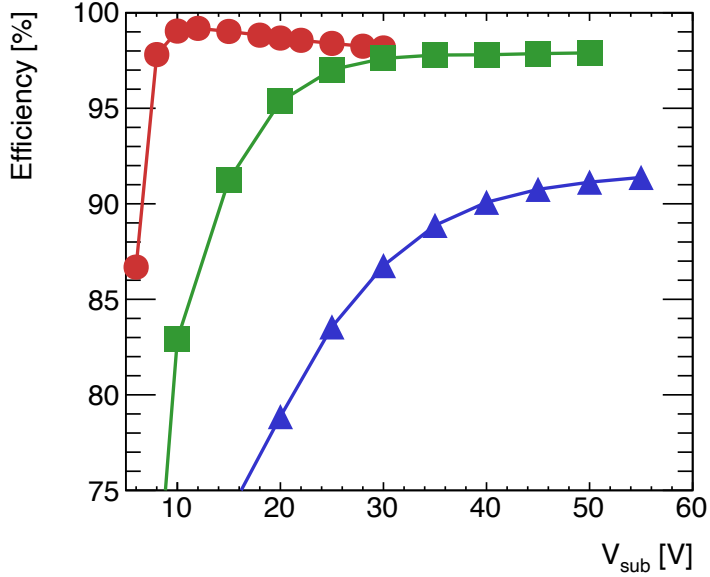


[G. Gustavino et al., \(VERTEX2023\)048](#)  
[M. van Rijnbach et al., Eur. Phys. J. C 84, 251 \(2024\)](#)

# MALTA2 irradiation study up to $3 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$

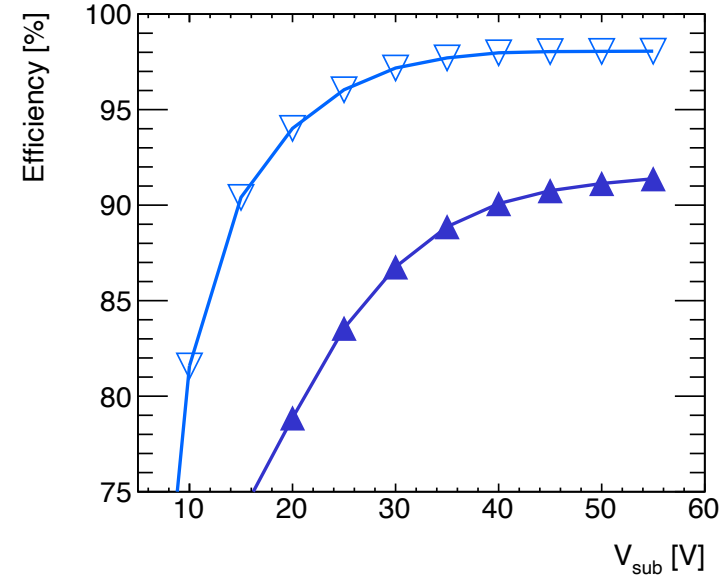
Efficiency > 90 % recovered by substrate voltage increase

Efficiency > 95% recovered for higher doping on continuous n-layer



**MALTA2**  
Cz, 100  $\mu\text{m}$ , H-dop  
back-metal, XDPW

- $1 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$
- $2 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$
- ▲  $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$



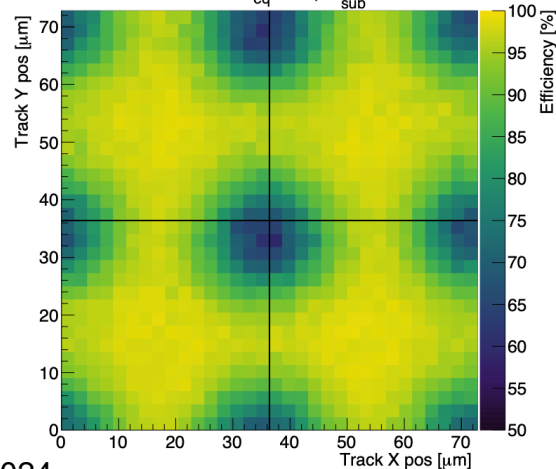
**MALTA2**  
Cz, 100  $\mu\text{m}$   
back-metal, XDPW  
 $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$

- ▽ VH-dop
- ▲ H-dop

- Backside metallisation  
→ good voltage propagation to substrate across chip
- Efficiency loss at pixel corners

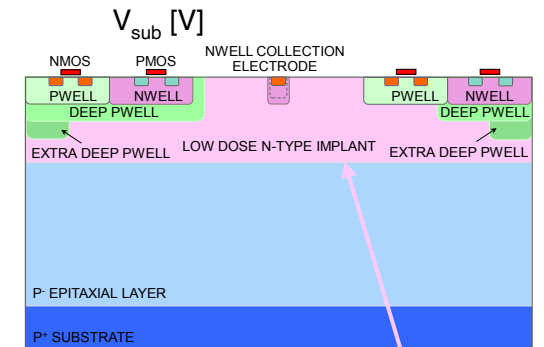
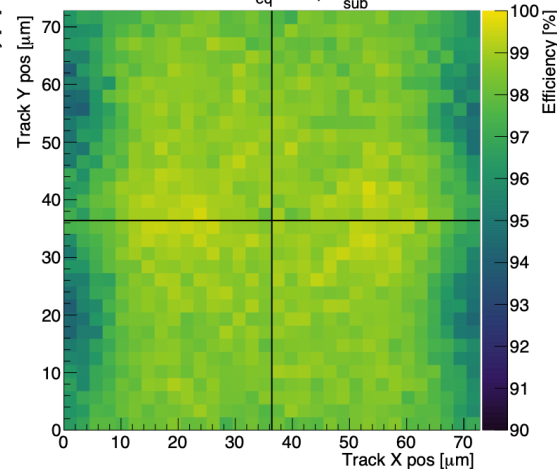
## ▲ High doping

**MALTA2**, Cz, 100 $\mu\text{m}$ , H-dop, XDPW  
 $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$ ,  $V_{\text{sub}} = -55 \text{ V}$



## ▽ Very high doping

**MALTA2**, Cz, 100 $\mu\text{m}$ , VH-dop, XDPW  
 $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$ ,  $V_{\text{sub}} = -55 \text{ V}$



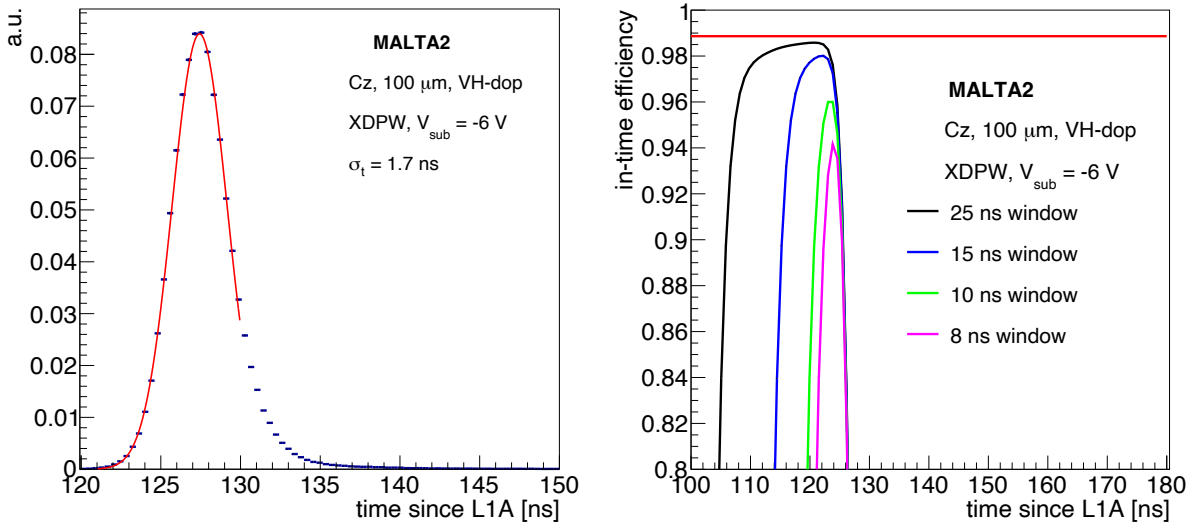
- VH-doping\* of n-type implant improves charge collection at pixel corners  
→ Improved lateral depletion

\*the doping level refers to the relative difference in implantation dose, approximately 70%.

[G. Gustavino et al., \(VERTEX2023\)048](#)  
[M. van Rijnbach et al., Eur. Phys. J. C 84, 251 \(2024\)](#)

# MALTA2 Timing

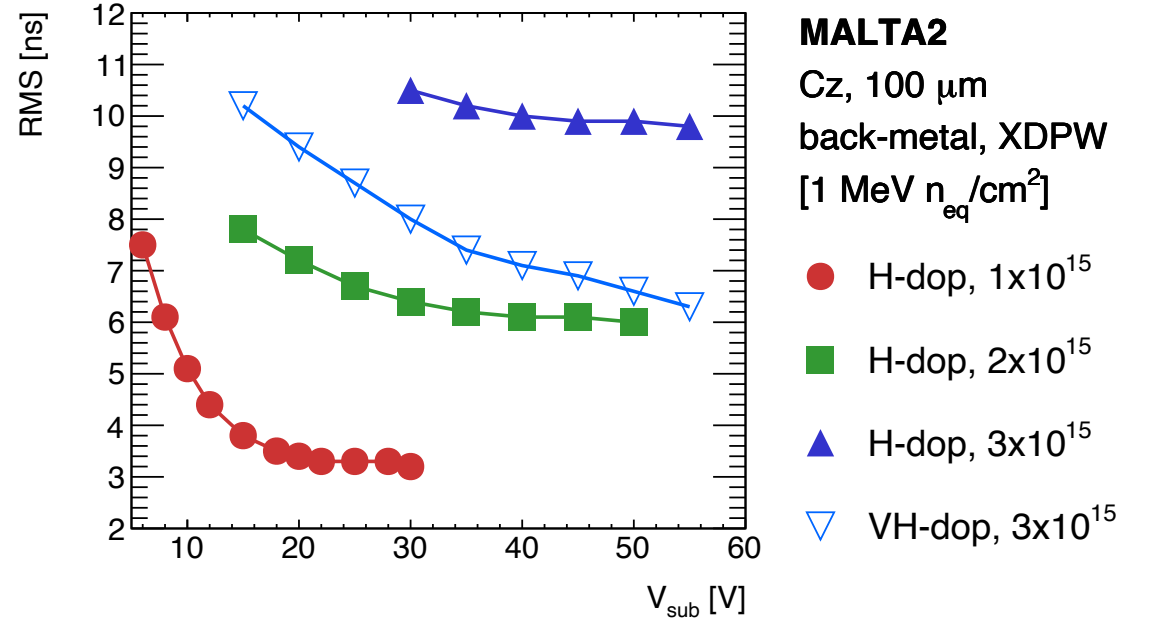
## Before irradiation



Time since L1A: Time of arrival of leading hit in a cluster w.r.t. scintillator reference

- $\sigma_t = 1.7 \text{ ns}$ 
  - scintillator jitter ( $\sim 0.5 \text{ ns}$ )
  - FPGA readout jitter ( $\sim 0.9 \text{ ns}$ )
  - Correction for signal propagation
- $> 98\%$  of hits collected within 25 ns window
- $> 90\%$  of hits collected within 8 ns window

## After irradiation



**Timing deteriorates** with irradiation

- due to charge trapping
- slow collection from pixel corners

**Timing improves** for

- Increase in substrate bias voltage

[G. Gustavino et al., \(VERTEX2023\)048](#)

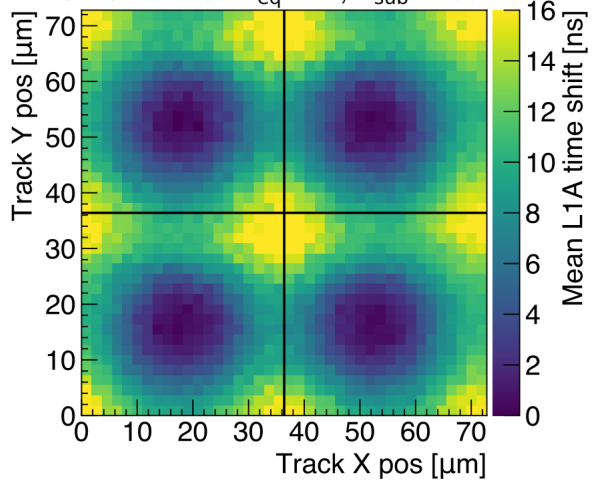
[M. van Rijnbach et al., Eur. Phys. J. C \*\*84\*\*, 251 \(2024\)](#)

# MALTA2 Timing

MALTA2 fulfills ATLAS ITk requirements in terms of efficiency and noise at  $3 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$

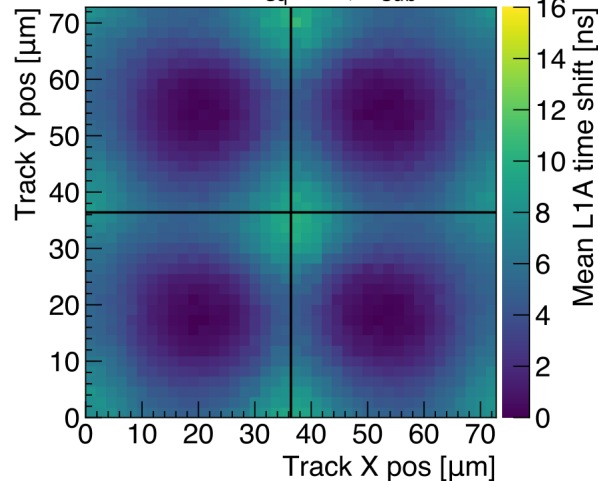
▲ High doping

MALTA2, Cz, 100 $\mu\text{m}$ , H-dop, XDPW  
 $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$ ,  $V_{\text{sub}} = -55 \text{ V}$

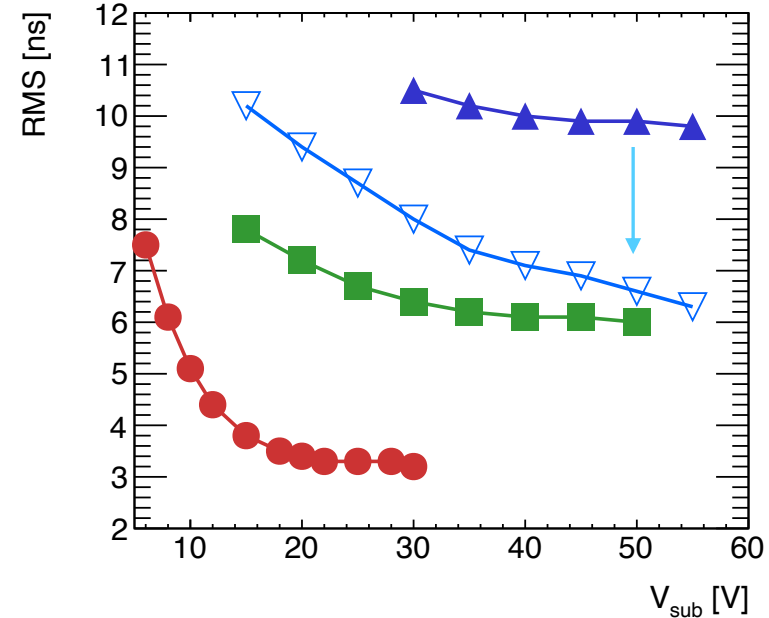


▽ Very high doping

MALTA2, Cz, 100 $\mu\text{m}$ , VH-dop, XDPW  
 $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$ ,  $V_{\text{sub}} = -55 \text{ V}$



## After irradiation



MALTA2

Cz, 100  $\mu\text{m}$   
 back-metal, XDPW  
 [1 MeV  $\text{n}_{\text{eq}}/\text{cm}^2$ ]

- H-dop,  $1 \times 10^{15}$
- H-dop,  $2 \times 10^{15}$
- ▲ H-dop,  $3 \times 10^{15}$
- ▽ VH-dop,  $3 \times 10^{15}$

**Timing deteriorates** with irradiation

- due to charge trapping
- slow collection from pixel corners

**Timing improves** for

- Increase in substrate bias voltage
- **Very high doping** prolongs „life-time“ of continuous n-layer
  - 95 % of hits collected within 25 ns (for  $3 \times 10^{15}$  !)
  - greater homogeneity of the mean time of the hit across the pixel

[G. Gustavino et al., \(VERTEX2023\)048](#)

[M. van Rijnbach et al., Eur. Phys. J. C 84, 251 \(2024\)](#)

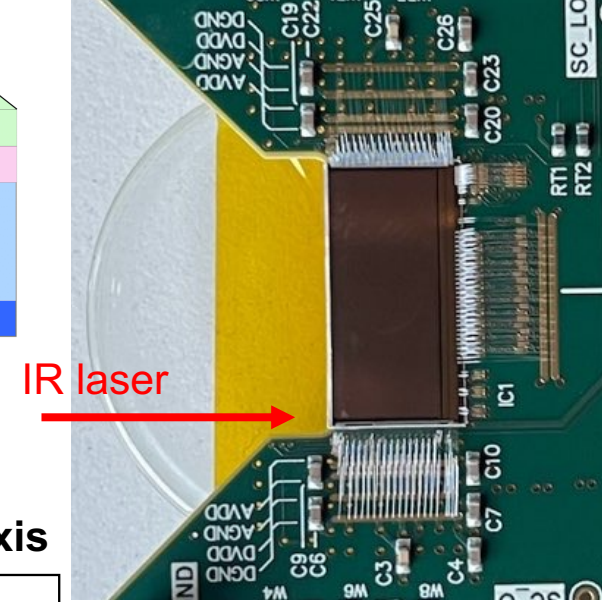
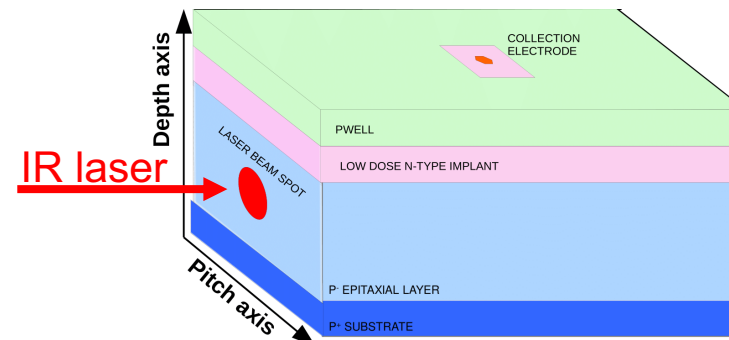


# Edge-TCT

**Aim of study:** Find depletion depth and cross check grazing angle studies with non irradiated, 30  $\mu\text{m}$  epitaxial sensor

**IR laser** (1064 nm, 500 Hz,  $\sim 4 \mu\text{m}$  beam width at focus)

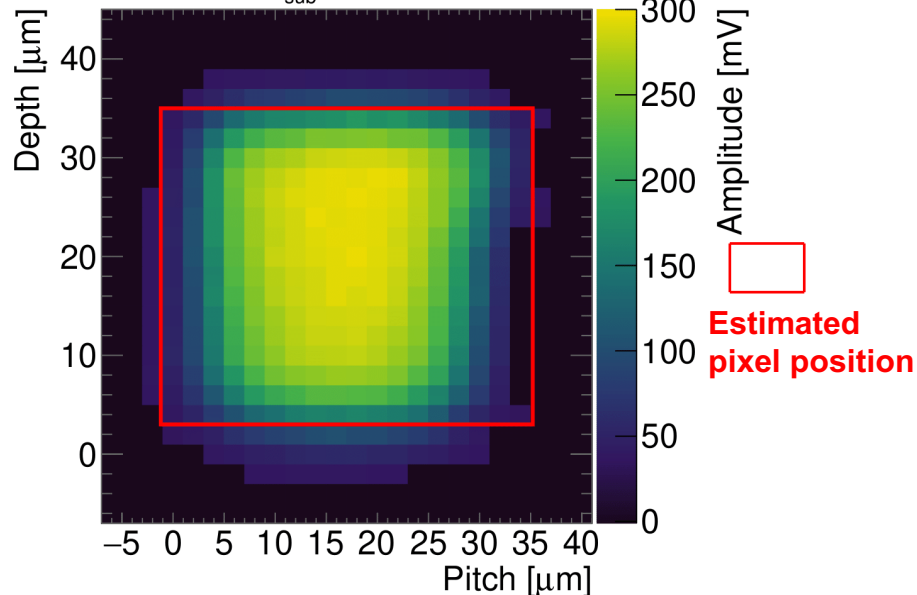
- Special PCB with free access to edge
  - Polished sensor edge
  - Analog pixels readout with oscilloscope
- Active depth of  $\sim 30 \mu\text{m}$  (as expected for epitaxial sample)  
 → Agrees with grazing angle studies



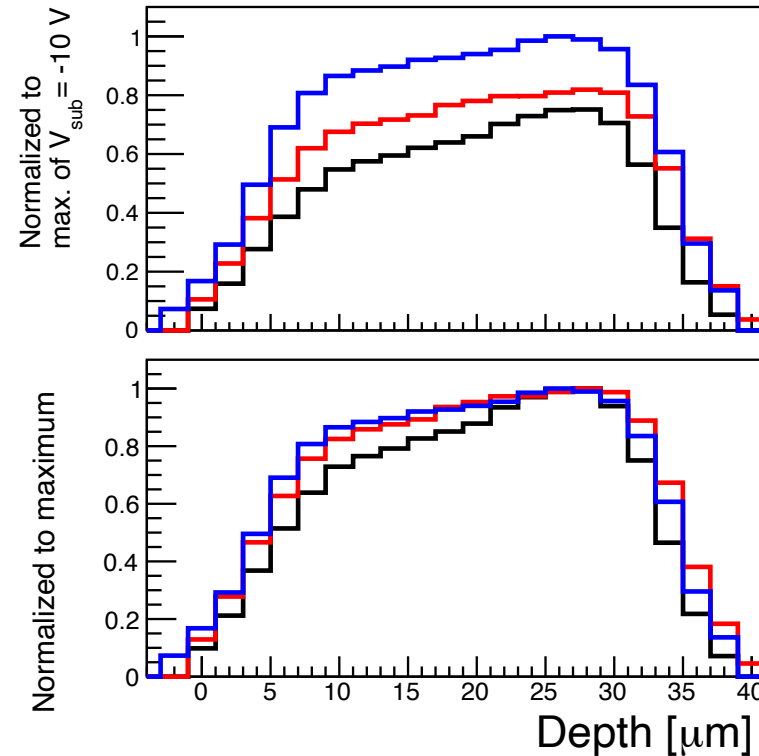
## Pixel cross section through edge

MALTA2, EPI 30, 100  $\mu\text{m}$ , L-dop, XDPW

$V_{\text{sub}} = -10 \text{ V}$



## Amplitude projection on depth axis



## MALTA2

EPI 30, 100  $\mu\text{m}$ , L-dop, XDPW

- $V_{\text{sub}} = -6 \text{ V}$   
FWHM =  $30.2 \pm 0.2 \mu\text{m}$
- $V_{\text{sub}} = -8 \text{ V}$   
FWHM =  $29.8 \pm 0.2 \mu\text{m}$
- $V_{\text{sub}} = -10 \text{ V}$   
FWHM =  $30.0 \pm 0.2 \mu\text{m}$

# Seed amplitude reconstruction from digital testbeam data

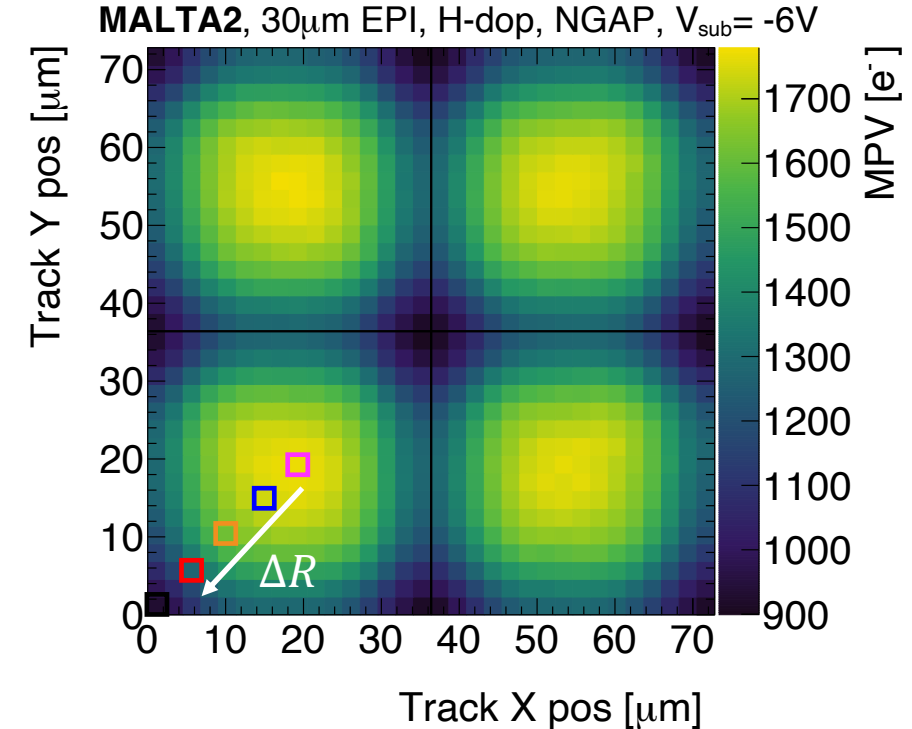
MALTA preliminary

**Aim of study:** Understanding charge collection in complicated pixel

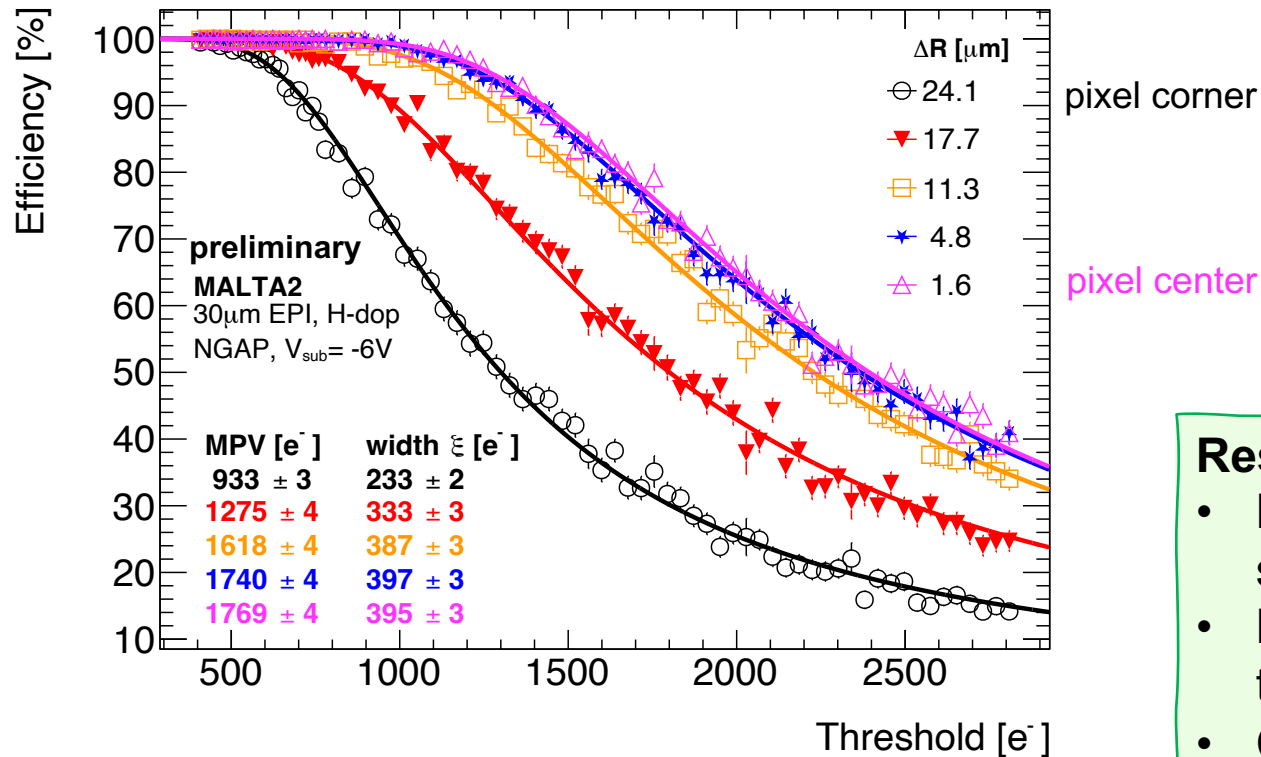
**Method:** Cumulative Landau distribution fitted to efficiency spectrum

- Amplitude reconstructable as most probable value (MPV)
- $\sigma_{track} = 4.5 \mu\text{m} < \text{pitch } 36.4 \mu\text{m} \rightarrow$  In-pixel resolution
- $\Delta R$  is distance to electrode at pixel center

In-pixel regions projected onto  $2 \times 2$  pixel matrix



## Selection of in-pixel regions along pixel diagonal



## Results:

- **Pixel center:**  $\sim 1800 e^-$  collected  $\rightarrow 30.2 \mu\text{m}$  active silicon depth (as expected for EPI sample)
- **Pixel corner:**  $\sim 900 e^-$  due to charge sharing and tracking uncertainty
- Charge reconstructed from **binary** data!
- Alternative to E-TCT or grazing angle studies

## Mini-MALTA3

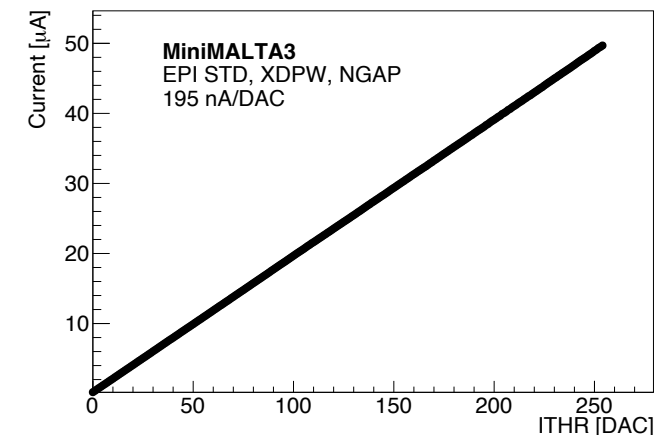
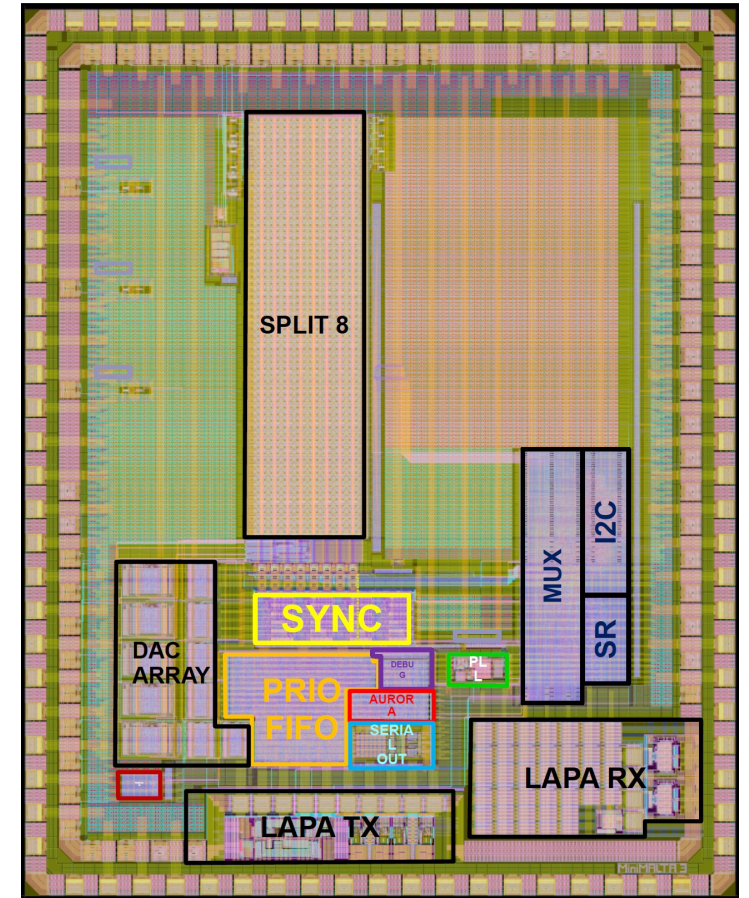
- 5×4 mm<sup>2</sup> demonstrator with 64 × 48 pixels
- Pixel size 36.4 × 36.4 μm<sup>2</sup> (same as MALTA2)
- Same front-end as MALTA2, no clock over the matrix
- Integrate **time-stamping** and **data serialiser on chip** in periphery
- Time-stamping logic at 1.28 GHz (for MALTA2 done in FPGA)  
→ **aiming for sub-nanosecond** on-chip timing resolution
- Synchronization memory with 0.78 ns time resolution
- Fast clock generation with STFC PLL from 80 MHz clock
- Serialized high-speed output

### Testing of the chip:

- arrived late 2023
- powered and consumption is within expected values
- Responding to the shift register slow control
- DAC scan results as expected

### More details:

“Radiation hard read-out architectures” (WG1 C. Solans) Tue 9:00



## Summary

**MALTA beam telescope @SPS with  $\sigma_s = 4.5 \mu\text{m}$  &  $\sigma_t = 2.1 \text{ ns}$**

**MALTA2 shows radiation hardness up to  $3 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$**

- > 98% efficiency
- > 95% of clusters collected within 25 ns (LHC bunch crossing window)
- Fulfills ATLAS ITk requirements for efficiency and noise

### Depletion depth studies:

- Edge-TCT
- Grazing angle studies
- Amplitude reconstruction from binary hit data

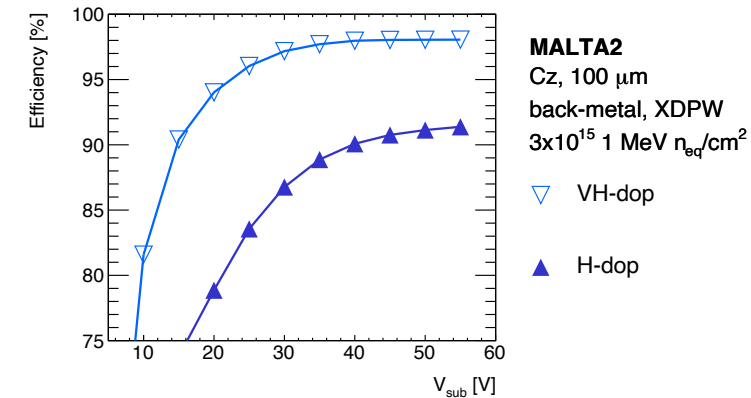
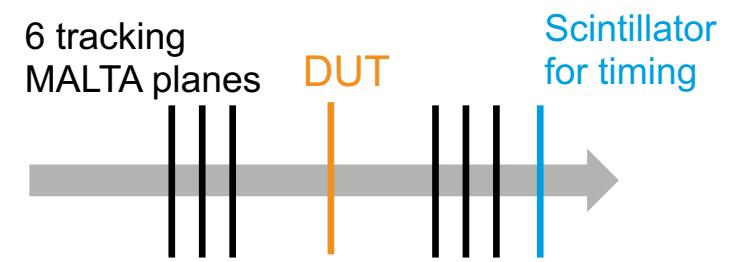
### MALTA3:

- Time-stamping logic on chip @ 1.28GHz aiming for **sub-nanosecond** timing
- Serialised data output in view of future detector integration

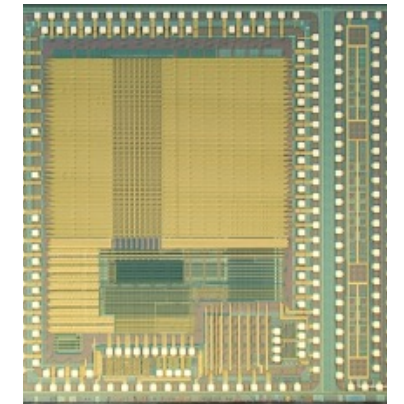
### Future developments:

“Radiation hard read-out architectures” (WG1 C. Solans) Tue 9:00

“Interconnections and multi-chip flex developments” (WG7 A. Sharma) Wed 13:30



**MALTA2**  
Cz, 100  $\mu\text{m}$   
back-metal, XDPW  
 $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$   
▽ VH-dop  
▲ H-dop



# Latest publications

M. van Rijnbach et al., Radiation Hardness of MALTA2 Monolithic CMOS Sensors on Czochralski Substrates, Eur. Phys. J. C 84 (2024) 251, [link](#)

D.V. Berlea et al., Depletion depth studies with the MALTA2 sensor, a depleted monolithic active pixel sensor, NIM A 1063 (2024) 169262, [link](#)

F. Dachs et al., Quad-module characterization with the MALTA monolithic pixel chip, NIM A 1064 (2024) 169306, [link](#)

C. Solans et al., MALTA monolithic Pixel sensors in TowerJazz 180 nm technology, NIM A 1057 (2023) 168787, [link](#)

F. Dachs et al., Development of a large-area, light-weight module using the MALTA monolithic pixel detector, NIM A 1047 (2023) 167809, [link](#)

H. Pernegger et al., MALTA-Cz: A radiation hard full-size monolithic CMOS sensor with small electrodes on high-resistivity Czochralski substrate, JINST 18 (2023) P09018, [link](#)

J. Weick et al., Development of novel low-mass module concepts based on MALTA monolithic pixel sensors, JINST 18 (2023) C04003, [link](#)

D. Drobijevic et al, Future developments of radiation tolerant sensors based on the MALTA architecture, JINST 18 (2023) C03013, [link](#)

G. Gustavino et al., Timing performance of radiation hard MALTA monolithic pixel sensors, JINST 18 (2023) C03011, [link](#)

V. Berlea et al, Radiation hardness of MALTA2, a monolithic active pixel sensor for tracking applications, TNS 70 (2023) 2303-2309, [link](#)

M. van Rijnbach et al., Performance of the MALTA Telescope, Eur. Phys. J. C 83 (2023) 581, [link](#)



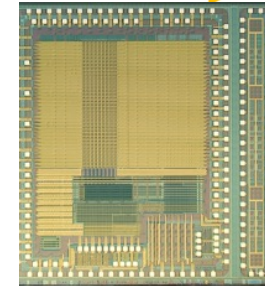
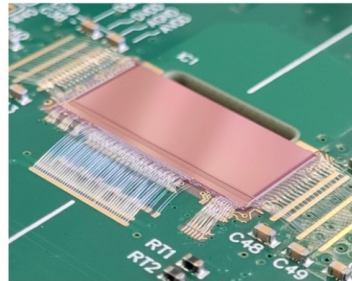
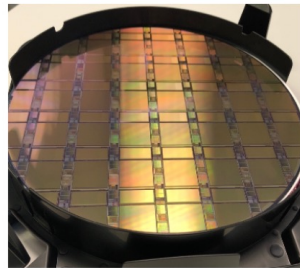
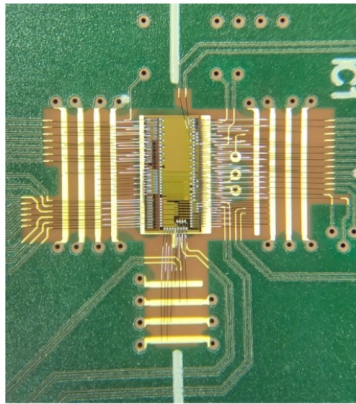
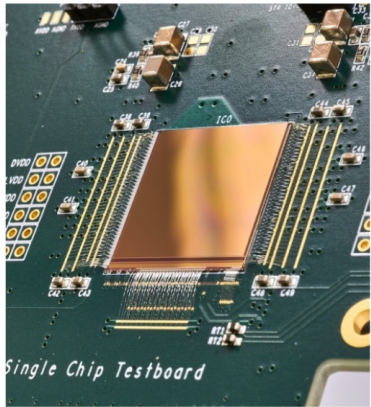
# Backup

# MALTA history

Based on R&D for ALPIDE

STREAM

AIDA Innova WP5 and  
CERN EP R&D WP 1.2



**MALTA1 & MLVL**

**Mini-MALTA**

**MALTA C**

**MALTA 2**

**MALTA 3**

**Jan 2018**

**Jan 2019**

**Aug 2019**

**Jan 2021**

**2023**

Large demonstrator  
Asynchronous readout  
Electrode size and reset  
mechanism evaluation

Small demonstrator  
Process and mask  
modification

Slow control  
improvements on EPI  
and Czochralski  
substrates

New front-end  
Additional process  
modification

Large matrix  
Time tagging

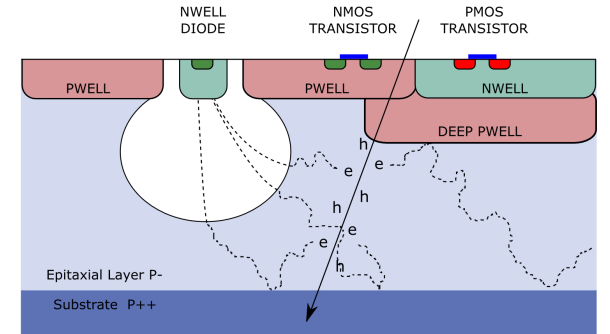
Poor lateral field after  
irradiation

Full efficiency after  
 $1e15 \text{ n/cm}^2$

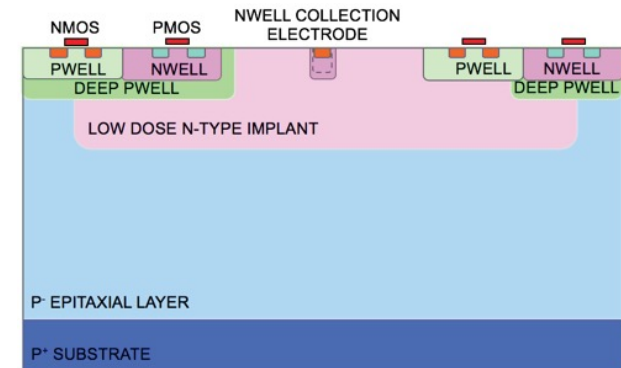
Enlarged cluster size and  
improved time resolution  
on Czochralski

Improved time resolution  
and on chip synchronization

Technology	180 nm Towerjazz
Sensor area	$9 \times 18 \text{ mm}^2$
Pixel pitch	$36.4 \times 36.4 \mu\text{m}^2$
Thickness	50 - 300 $\mu\text{m}$

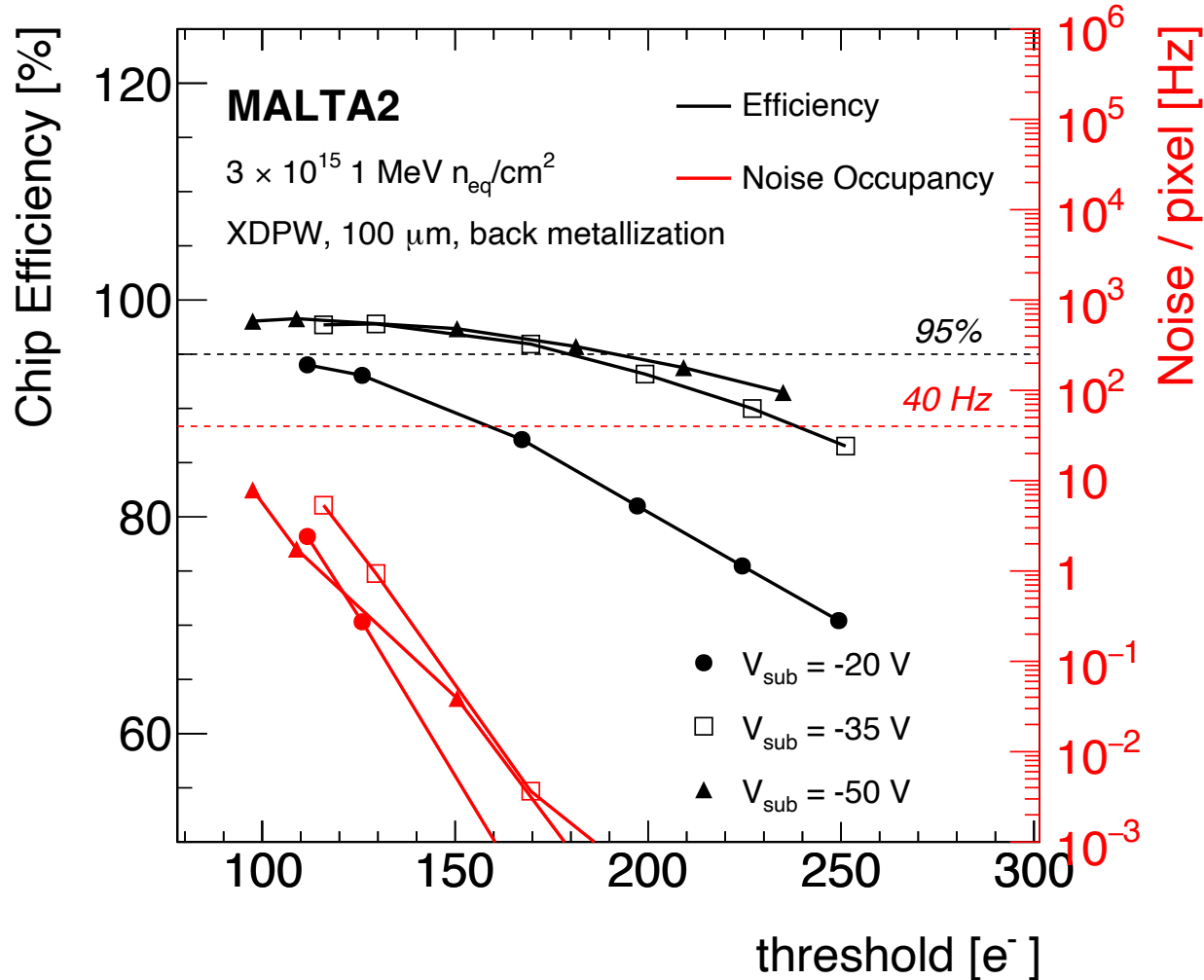
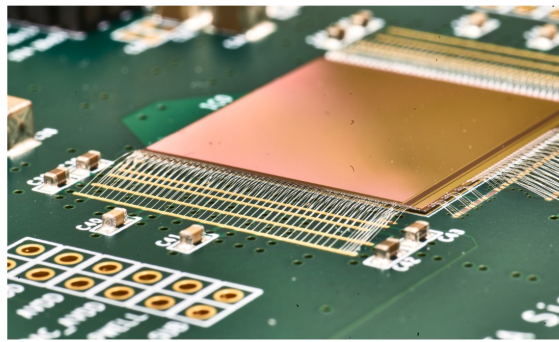


Additional implant increases  
depletion zone and electric field

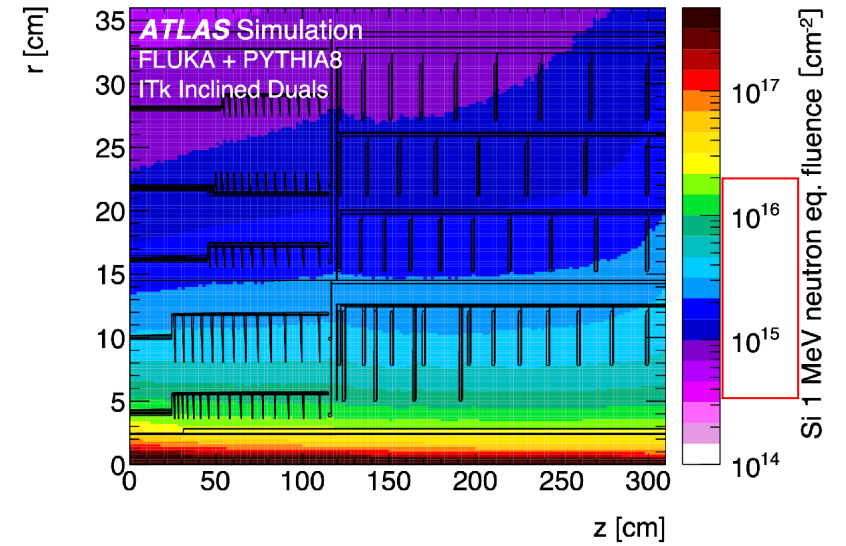


# MALTA2 Performance

## Irradiation summary



## Fluence distribution for the ATLAS ITk



Fulfills requirements for ATLAS HL-LHC ITk pixel upgrade in terms of:

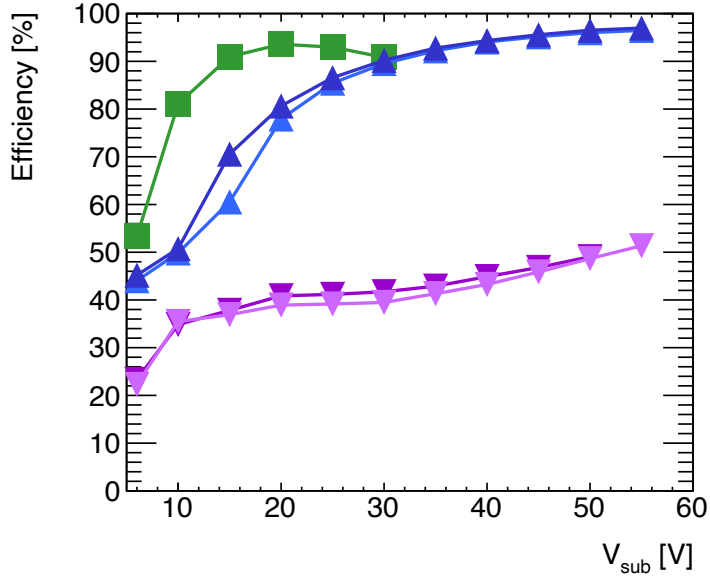
- Radiation hardness up to  $3 \times 10^{15} n_{eq}/cm^2$  (~ HL fluence 10 cm from beam pipe)
- Efficiency > 95%
- Noise rate < 40 Hz
- Timing resolution of 2.1 ns



# MALTA2 irradiation study up to $5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$

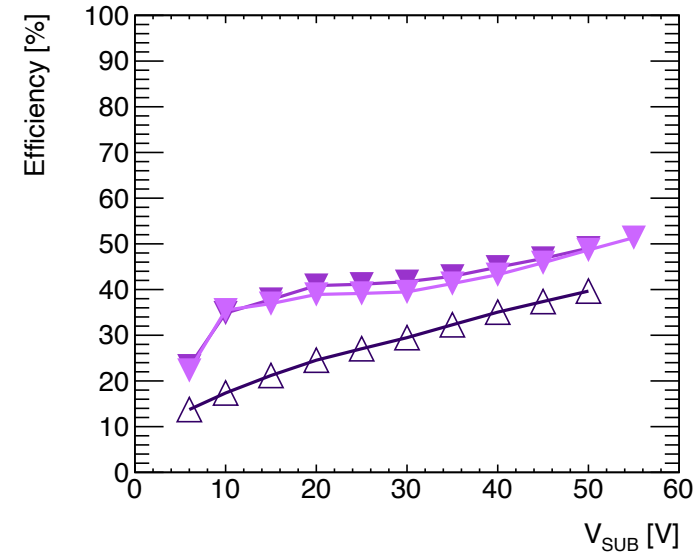
Efficiency ~35 % recovered by substrate voltage increase

Efficiency ~50% recovered for higher doping on continuous n-layer



**MALTA2**  
Cz, 100  $\mu\text{m}$ , VH-dop  
fiducial region, XDPW

- $2 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$
- ▲  $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$
- ▲  $3 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$
- ▼  $5 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$
- ▼  $5 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$

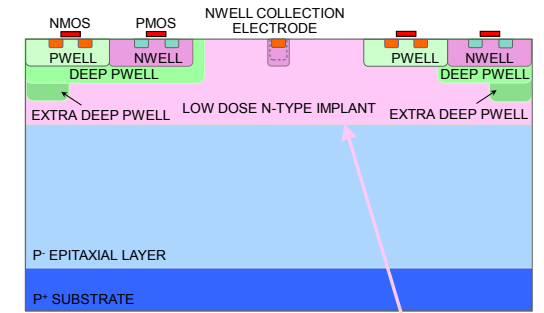
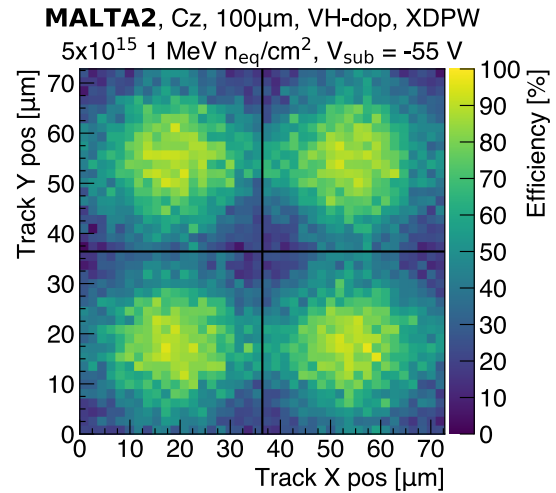
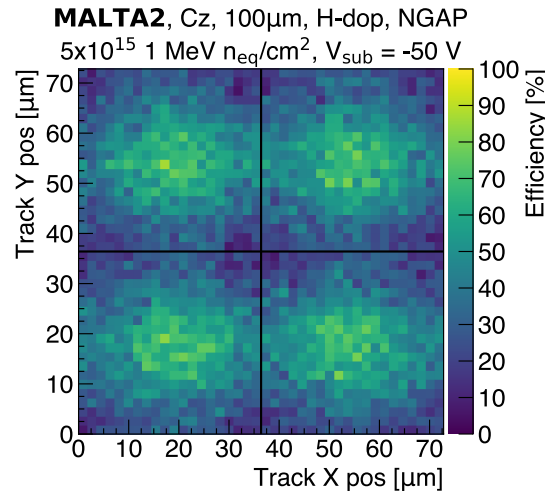


**MALTA2**  
Cz, 100  $\mu\text{m}$ , fiducial region  
 $5 \times 10^{15} \text{ 1 MeV n}_{\text{eq}}/\text{cm}^2$

- △ H-dop, NGAP
- ▼ VH-dop, XDPW
- ▼ VH-dop, XDPW

△ High doping

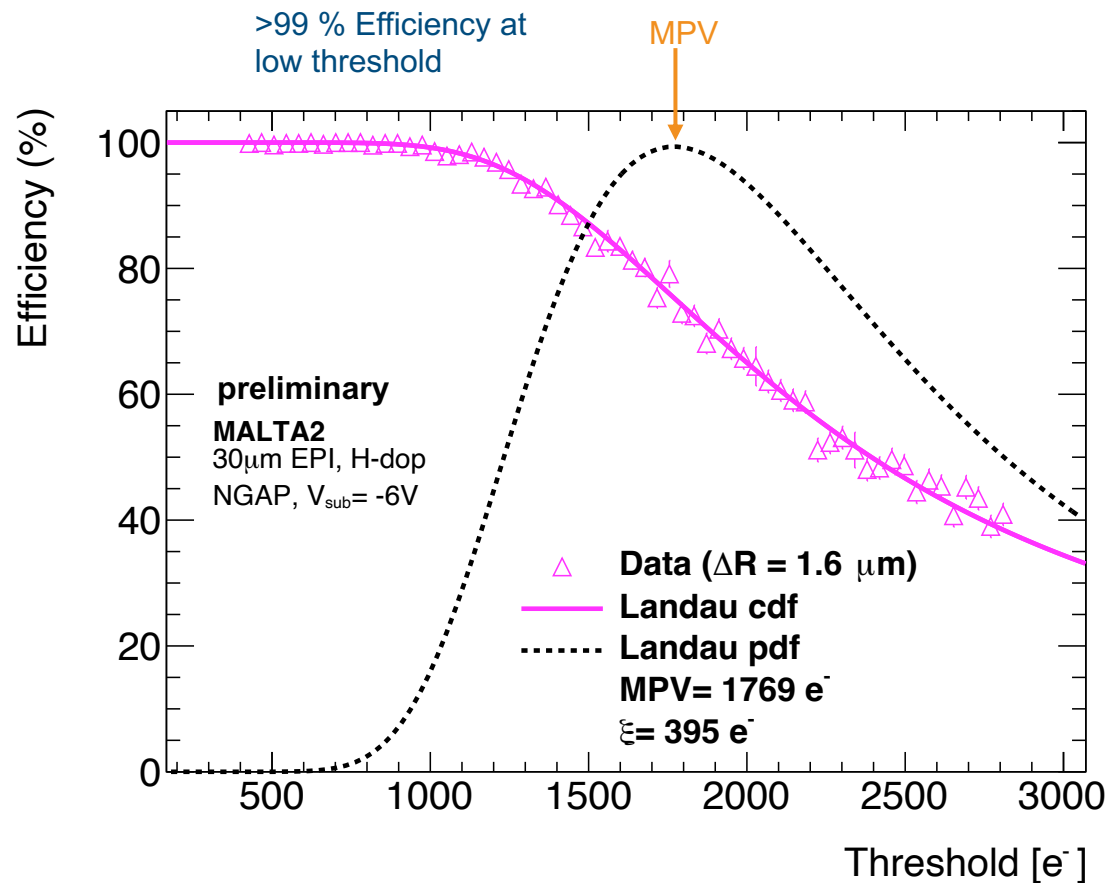
▼ Very high doping



• VH-doping\* of n-type implant improves charge collection at pixel center and corners  
→ Improved overall depletion

\*the doping level refers to the relative difference in implantation dose, approximately 70%.

# Amplitude reconstruction method from binary data



- Reconstruct tracks with telescope
- Efficiency =  $\frac{\text{Tracks detected in DUT}}{\text{Tracks reconstructed with telescope}}$
- Energy loss of charged hadrons (MIPs): Landau probability density function (**pdf**)
- Cumulative Landau distribution (**cdf**) fitted to efficiency data
- Most probable value (MPV) of Landau is
  - Maximum of **pdf**
  - Inflection point of **cdf**